



# Bipolar NPN Bare Die – BTN6041

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## Part Description

The BTN6041 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

## Key Parameters:

- VCBO = 20V
- VCEO = 12V
- VEBO = 9V
- hFE = 355-800 @ VCE = 2V, IC = 0.5A
- VCE(Sat) = 0.8V @ IC = 3A, IB = 100mA
- fT = 150 MHz @ VCE = 6V, IE = 0A
- COBO = 50pF @ VCB = 10V

## Features

Low VCE(sat) high hFE

## Die Size (Unawn)

840µm X 840µm, 33 Mils X 33 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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